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(54) **ORGANIC LIGHT EMITTING DISPLAY
DEVICE AND METHOD FOR
MANUFACTURING THE SAME**

USPC 257/40, 99, 100, 708, E33.059
See application file for complete search history.

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(30) **Foreign Application Priority Data**

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(57) **ABSTRACT**

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H01L 51/56 (2006.01)

H01L 51/52 (2006.01)

H01L 27/32 (2006.01)

(52) **U.S. Cl.**

CPC **H01L 51/56** (2013.01); **H01L 27/3276**
(2013.01); **H01L 51/5203** (2013.01); **H01L**
51/5243 (2013.01)

Discussed is an organic light emitting display device which prevents a voltage drop, wherein the light emitting display device includes a substrate; a first electrode on the substrate; an organic light emitting layer on the first electrode; a second electrode on the substrate including the organic light emitting layer; and an encapsulation substrate confronting the substrate, wherein the encapsulation substrate is formed of a metal material, and is electrically connected with the second electrode.

(58) **Field of Classification Search**

CPC H01L 51/5243; H01L 51/5228; H01L
51/5225

12 Claims, 6 Drawing Sheets

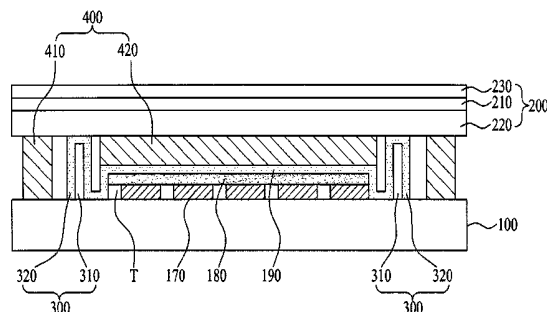
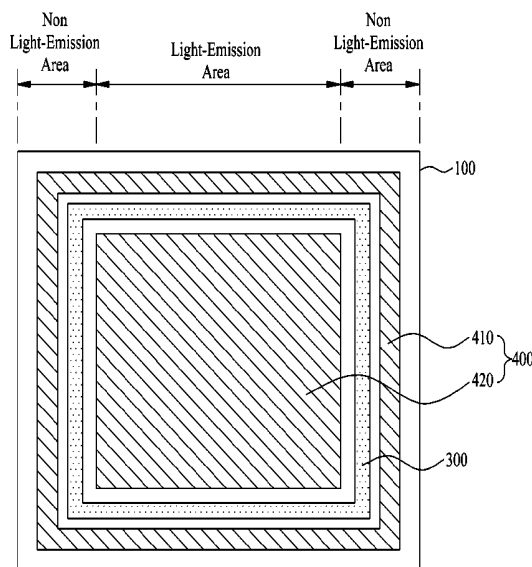


FIG. 1

Related Art

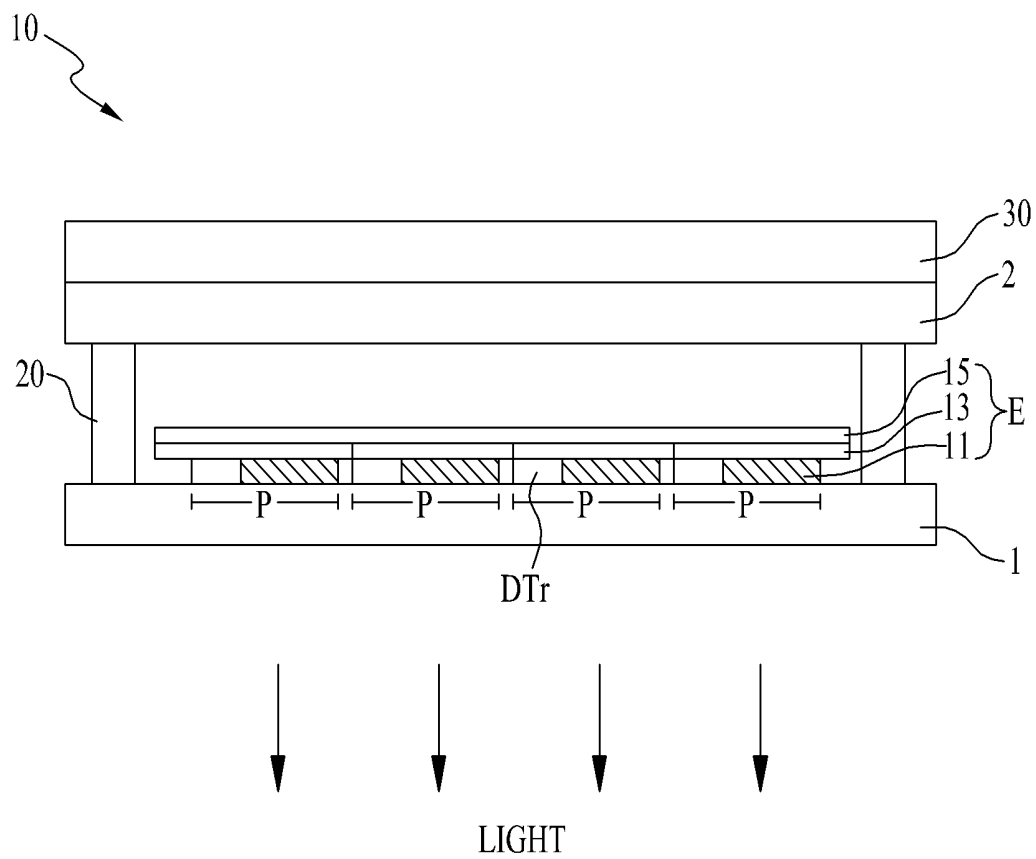


FIG. 2

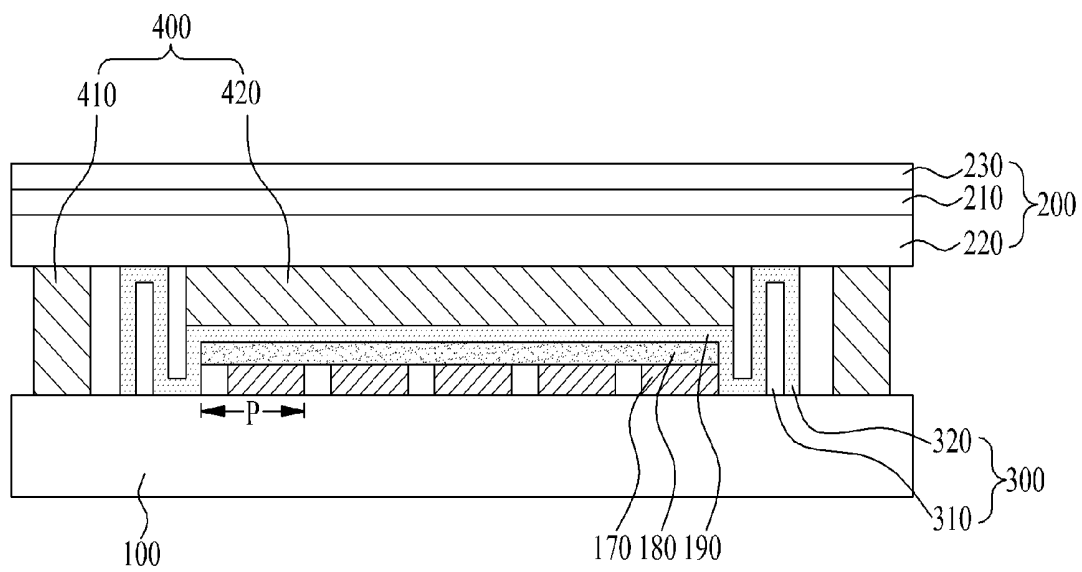


FIG. 3

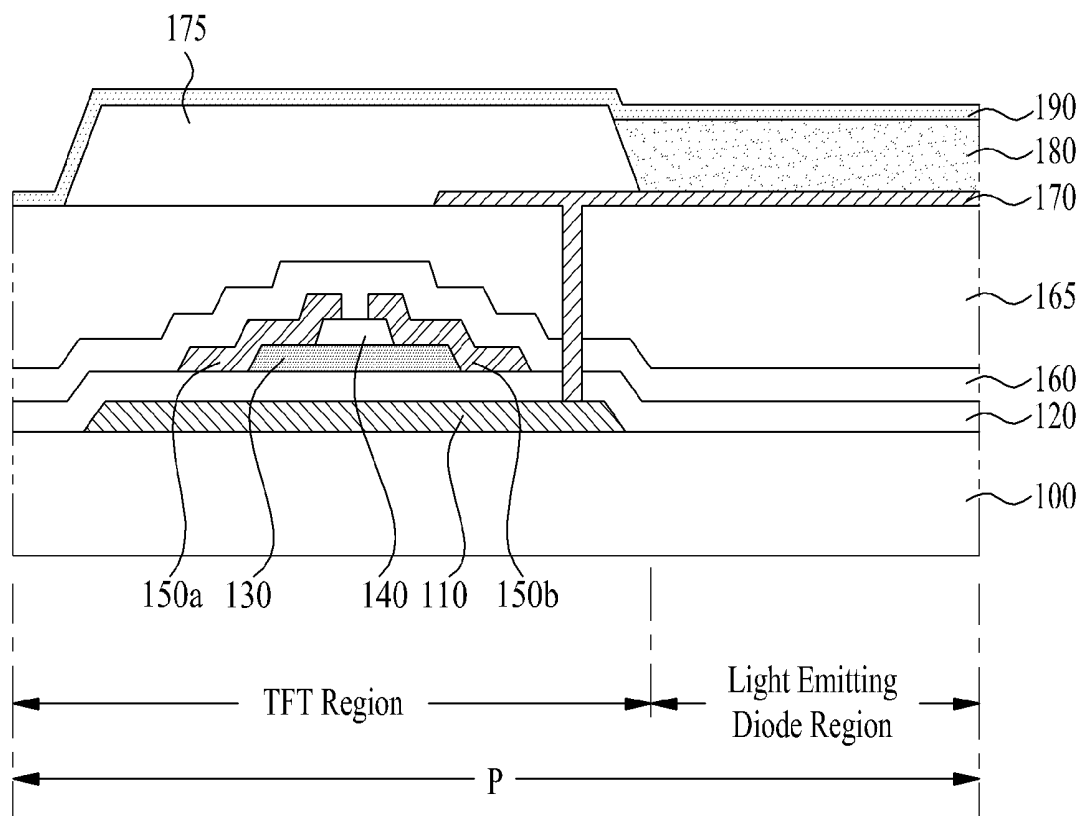


FIG. 4

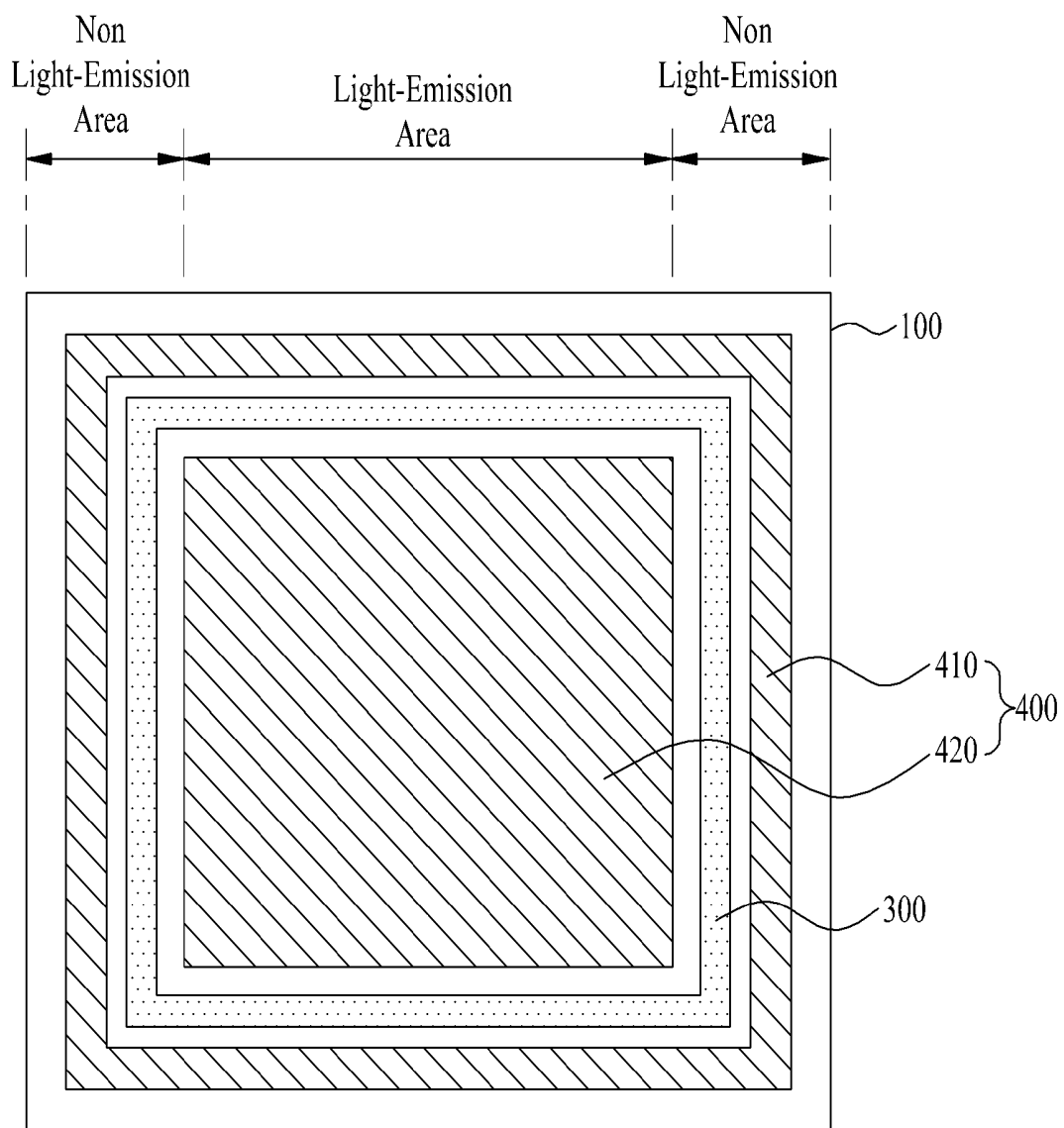


FIG. 5A

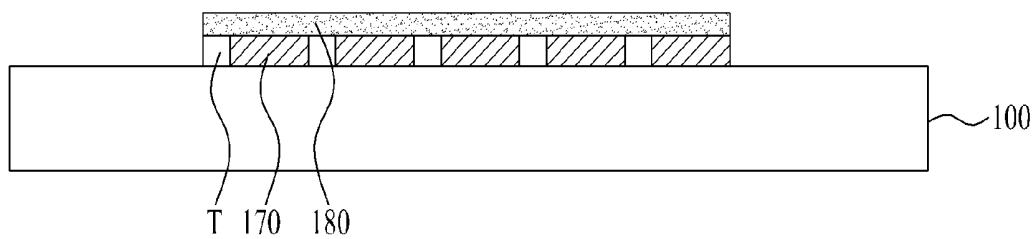


FIG. 5B

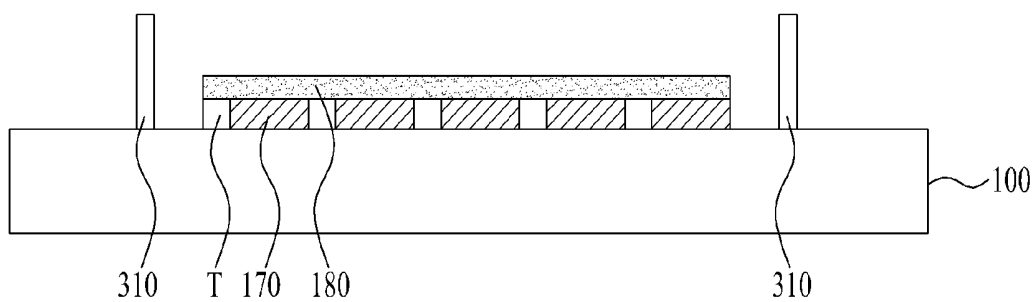


FIG. 5C

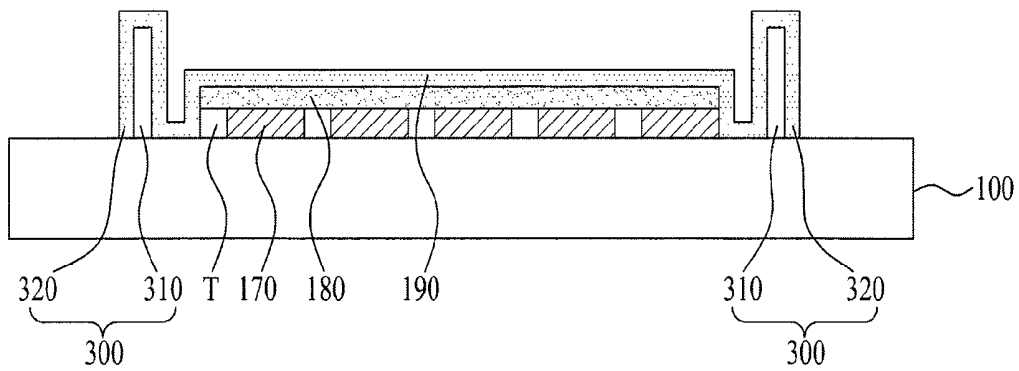
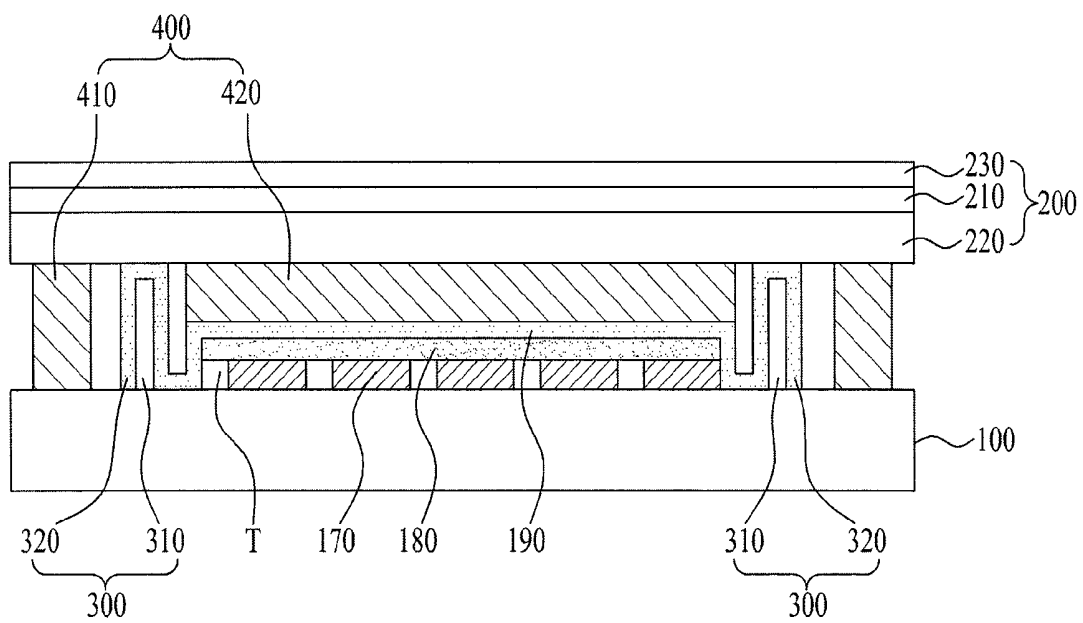


FIG. 5D



ORGANIC LIGHT EMITTING DISPLAY DEVICE AND METHOD FOR MANUFACTURING THE SAME

CROSS REFERENCE TO RELATED APPLICATIONS

This application claims the benefit of the Korean Patent Application No. 10-2012-0139929 filed on Dec. 4, 2012, which is hereby incorporated by reference as if fully set forth herein.

BACKGROUND

1. Field of the Invention

Embodiments of the present invention relate to an organic light emitting display device and a method for manufacturing the same.

2. Discussion of the Related Art

According to a recent development of multimedia, there is an increasing demand for a flat panel display. In order to satisfy this increasing demand, various flat panel displays such as liquid crystal display device, plasma display panel, and organic light emitting display device are practically used. Among the various flat panel displays, the organic light emitting display device has been attracted great attentions owing to a rapid response speed. In addition, since internal elements included in the organic light emitting display device are formed of a solid material, the organic light emitting display device has good durability against external forces, and also enables a wide range of use temperature.

Especially, a manufacturing process of the organic light emitting display device is simplified so that it is possible to reduce a manufacturing cost in comparison to a related art liquid crystal display device.

FIG. 1 illustrates an organic light emitting display device of a bottom emission type according to the related art.

As shown in FIG. 1, the organic light emitting display device 10 include a first substrate 1, and a second substrate 2 confronting the first substrate 1, wherein the first substrate 1 and the second substrate 2 are provided with a predetermined interval in-between, and are encapsulated and bonded to each other by the use of sealing pattern 20 provided along the edges thereof.

In more detail, a driving thin film transistor (DTr) is formed in each of pixel regions (P) on the first substrate 1. Also, a first electrode 11, an organic light emitting layer 13, and a second electrode 15, which constitute a light emitting diode (E), are sequentially deposited on the first substrate 1. The first electrode 11 is electrically connected with the driving thin film transistor (DTr).

In this case, the first electrode 11 is formed of a transparent conductive material, and the second electrode 15 is formed of an opaque conductive material. Accordingly, light emitted from the organic light emitting layer is guided toward the first electrode 11.

Meanwhile, in order to prevent a lifespan of the organic light emitting display device 10 from being shortened by heat generated for a driving mode and degradation of the driving thin film transistor (DTr), as shown in FIG. 1, a heat insulating plate 30 is attached to an outer surface of the second substrate 2.

According as the organic light emitting display device of the related art is increased in size, an area of the second electrode 15 is increased so that a resistance value is increased, whereby a voltage drop (IR drop) might occur. Also, power consumption is increased by the increase of

voltage drop according to the increase of resistance in the second electrode 15, and luminance of the organic light emitting display device is not uniform, whereby it is difficult to realize good reliability in the organic light emitting display device.

There has been proposed a method for increasing a thickness of the second electrode 15 so as to prevent the voltage drop caused by the increase of resistance in the second electrode 15. However, even though the voltage drop can be prevented owing to the increased thickness of the second electrode 15, a manufacturing cost of the organic light emitting display device is raised, and the organic light emitting display device is increased in its weight and thickness.

Especially, since the organic light emitting display device of the related art uses the carbon-based heat insulating plate, the organic light emitting display device of the related art is more increased in its weight and thickness.

SUMMARY

Accordingly, embodiments of the present invention are directed to an organic light emitting display device and a method for manufacturing the same that substantially obviates one or more problems due to limitations and disadvantages of the related art.

An aspect of embodiments of the present invention is to provide an organic light emitting display device which is capable of preventing a voltage drop, and a method for manufacturing the same.

Another aspect of embodiments of the present invention is to provide an organic light emitting display device which has light weight and thin thickness, and a method for manufacturing the same.

Additional advantages and features of the invention will be set forth in part in the description which follows and in part will become apparent to those having ordinary skill in the art upon examination of the following or may be learned from practice of the invention. The objectives and other advantages of the invention may be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

To achieve these and other advantages and in accordance with the purpose of the invention, as embodied and broadly described herein, there is provided an organic light emitting display device that may include a substrate; a first electrode on the substrate; an organic light emitting layer on the first electrode; a second electrode on the substrate including the organic light emitting layer; and an encapsulation substrate confronting the substrate, wherein the encapsulation substrate is formed of a metal material, and is electrically connected with the second electrode.

In another aspect of an embodiment of the present invention, there is provided a method for manufacturing an organic light emitting display device that may include forming a first electrode on a predetermined region of a substrate; forming an organic light emitting layer on the first electrode; forming a second electrode on the substrate including the organic light emitting layer; and bonding an encapsulation substrate of a metal material to the substrate so as to electrically connect the encapsulation substrate and the second electrode to each other.

It is to be understood that both the foregoing general description and the following detailed description of the

present invention are exemplary and explanatory and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

The accompanying drawings, which are included to provide a further understanding of the invention and are incorporated in and constitute a part of this application, illustrate embodiment(s) of the invention and together with the description serve to explain the principle of the invention. In the drawings:

FIG. 1 is a cross sectional view illustrating an organic light emitting display device according to the related art;

FIG. 2 is a cross sectional view illustrating an organic light emitting display device according to one embodiment of the present invention;

FIG. 3 is a cross sectional view illustrating a pixel of FIG. 2;

FIG. 4 is a plane view illustrating the organic light emitting display device according to one embodiment of the present invention; and

FIGS. 5A to 5D are cross sectional views illustrating a process for manufacturing the organic light emitting display device according to one embodiment of the present invention.

DETAILED DESCRIPTION OF THE INVENTION

Reference will now be made in detail to the exemplary embodiments of the present invention, examples of which are illustrated in the accompanying drawings. Wherever possible, the same reference numbers will be used throughout the drawings to refer to the same or like parts.

On explanation about the embodiments of the present invention, the following details about the terms should be understood.

The term of a singular expression should be understood to include a multiple expression as well as the singular expression if there is no specific definition in the context. If using the term such as “the first” or “the second”, it is to separate any one element from other elements. Thus, a scope of claims is not limited by these terms.

Also, it should be understood that the term such as “include” or “have” does not preclude existence or possibility of one or more features, numbers, steps, operations, elements, parts or their combinations.

It should be understood that the term “at least one” includes all combinations related with any one item. For example, “at least one among a first element, a second element and a third element” may include all combinations of the two or more elements selected from the first, second and third elements as well as each element of the first, second and third elements.

Also, if it is mentioned that a first element is positioned “on or above” a second structure, it should be understood that the first and second elements may be brought into contact with each other, or a third element may be interposed between the first and second elements. However, if using “right on or right above”, it should be understood that the first and second elements are brought into contact with each other.

Hereinafter, an organic light emitting display device according to embodiments of the present invention and a method for manufacturing the same will be described in detail with reference to the accompanying drawings.

FIG. 2 is a cross sectional view illustrating an organic light emitting display device according to one embodiment of the present invention.

Generally, according to a transmission direction of emitted light, an organic light emitting display device may be classified into a top emission type and a bottom emission type. Referring to FIG. 2, the organic light emitting display device according to one embodiment of the present invention may be the bottom emission type.

As shown in FIG. 2, the organic light emitting display device according to one embodiment of the present invention may include a substrate 100, an encapsulation substrate 200, an auxiliary electrode 300, and a sealing pattern 400.

First, the substrate 100 may include a thin film transistor (TFT) region and a light emitting diode region. A pixel (P) may be defined by combination of the TFT region and the light emitting diode region.

A thin film transistor formed in the TFT region of the substrate 100 and a light emitting diode formed in the light emitting diode region will be described in detail with reference to FIG. 3.

FIG. 3 is a cross sectional view illustrating the expanded pixel shown in FIG. 2. As shown in FIG. 3, the thin film transistor including a gate electrode 110, an active layer 130, an etch stopper 140, a source electrode 150a and a drain electrode 150b is formed in the TFT region. Although not shown, a color filter layer may be additionally formed in the TFT region.

Also, the light emitting diode including a first electrode 170, an organic light emitting layer 180 and a second electrode 190 is formed in the light emitting diode region.

In more detail, the organic light emitting display device according to one embodiment of the present invention may include the substrate 100, the gate electrode 110, a gate insulating film 120, the active layer 130, the etch stopper 140, the source electrode 150a, the drain electrode 150b, a passivation film 160, a planarization layer 165, the first electrode 170, a bank layer 175, the organic light emitting layer 180, and the second electrode 190.

Generally, the substrate 100 is formed of glass. However, the substrate 100 may be formed of transparent plastic with flexibility, for example, polyimide. If forming the substrate 100 of polyimide, it is necessary to use polyimide with good heat-resistance, which endures a high temperature, due to a high-temperature deposition process on the substrate 100.

The gate electrode 110 is patterned on the substrate 100. The gate electrode 110 may be formed of molybdenum (Mo), aluminum (Al), chrome (Cr), aurum (Au), titanium (Ti), nickel (Ni), neodymium (Nd), copper (Cu), or their alloys. Also, the gate electrode 110 may be formed in a single-layered structure of the above metal materials or their alloys, or may be formed in a multi-layered structure of the above metal materials or their alloys.

The gate insulating film 120 is formed on the gate electrode 110, wherein the gate insulating film 120 electrically insulates the gate electrode 110 from the active layer 130. The gate insulating film 120 may be formed of an inorganic insulating material such as silicon oxide or silicon nitride, but not limited to these materials. For example, the gate insulating film 120 may be formed of an organic insulating material such as photoacryl or benzocyclobutene (BCB).

The active layer 130 is patterned on the gate insulating film 120. The active layer 130 may overlap with the gate electrode 110. The active layer 130 may be formed of an oxide semiconductor such as In—Ga—Zn—O (IGZO), but

not limited to this material. For example, the active layer **130** may be formed of a silicon-based semiconductor.

The etch stopper **140** is patterned on the active layer **130**. The etch stopper **140** prevents a channel region of the active layer **130** from being etched during an etching process for patterning the source electrode **150a** and the drain electrode **150b**. The etch stopper **140** may be formed of an inorganic insulating material such as silicon oxide or silicon nitride, but not limited to these materials. If needed, it is possible to omit the etch stopper **140**.

The source electrode **150a** and the drain electrode **150b** facing each other are patterned on the etch stopper **140**. The source electrode **150a** provided on the etch stopper **140** extends in one direction of the active layer **130**, whereby the extending source electrode **150a** is connected with the active layer **130**. Meanwhile, the drain electrode **150b** provided on the etch stopper **140** extends in the other direction of the active layer **130**, whereby the extending drain electrode **150b** is connected with the active layer **130**. The source electrode **150a** and the drain electrode **150b** may be formed of molybdenum (Mo), aluminum (Al), chrome (Cr), aurum (Au), titanium (Ti), nickel (Ni), neodymium (Nd), copper (Cu), or their alloys. Also, each of the source electrode **150a** and the drain electrode **150b** may be formed in a single-layered structure of the above metal materials or their alloys, or may be formed in a multi-layered structure of the above metal materials or their alloys.

The passivation film **160** is formed on the source electrode **150a** and the drain electrode **150b**. The passivation film **160** may be formed of an inorganic insulating material such as silicon oxide or silicon nitride, but not limited to these materials. For example, the passivation film **160** may be formed of an organic insulating material such as photoacryl or benzocyclobutene (BCB).

The planarization layer **165** is formed on the gate insulating film **120**, thereby enabling good step coverage of the organic light emitting display device. The planarization layer **165** may be formed of an organic insulating material such as photoacryl or benzocyclobutene (BCB).

The first electrode **170** is patterned on the planarization layer **165**. The first electrode **170** is connected with the drain electrode **150b** through a contact hole provided in the planarization layer **165** and the passivation film **160**. The organic light emitting display device according to the present invention is the bottom emission type. Thus, the first electrode **170** may be formed of a transparent conductive material having a high work function value, for example, Indium-Tin-Oxide (ITO) or Indium-Zinc-Oxide (IZO), whereby the first electrode **170** may function as an anode electrode.

The bank layer **175** is formed on the planarization layer **165**. In detail, the bank layer **175** is patterned to overlap with the thin film transistor, and the light emitting diode region is defined by the bank layer **175**. The bank layer **175** may be formed of an organic insulating material, for example, polyimide, photoacryl or benzocyclobutene (BCB), but not limited to these materials.

The organic light emitting layer **180** is formed on the first electrode **170**. Although not shown, the organic light emitting layer **180** may be formed in a deposition structure of hole injection layer/hole transport layer/organic light emitting layer/electron transport layer/electron injection layer. In this case, it is possible to omit one, two or more layers among the hole injection layer, the hole transport layer, the electron transport layer and the electron injection layer. The organic light emitting layer **180** may emit the light having the same color for the respective pixels, for example,

white-colored light, or may emit the light having the different colors for the respective pixels, for example, red-colored light, green-colored light, or blue-colored light.

The second electrode **190** is formed on the organic light emitting layer **180**. The second electrode **190** may be commonly applied to all pixels without being divided by each pixel. That is, the second electrode **190** may be formed on the bank layer **175** as well as the organic light emitting layer **180**. As mentioned above, the organic light emitting display device according to the present invention is the bottom emission type. Thus, the second electrode **190** may be formed of an opaque conductive material, whereby the second electrode **190** may function as a cathode electrode. For example, the second electrode **190** may be formed of a metal material whose work function value is relatively lower than that of the first electrode **170**, for example, any one metal material selected from aluminum (Al), aluminum alloy (AlNd), argentum (Ag), magnesium (Mg), aurum (Au) and aluminum magnesium alloy (AlMg).

The thin film transistor shown in FIG. 3 is only one example. That is, the thin film transistor may vary in structure. For example, the thin film transistor of FIG. 3 has a bottom gate structure where the gate electrode **110** is provided below the active layer **130**. According to a modified embodiment of the present invention, the thin film transistor may have a top gate structure where the gate electrode **110** is provided above the active layer **130**.

Referring once again to FIG. 2, the encapsulation substrate **200** is bonded to the substrate **100** while being confronted with the substrate **100**, which enables encapsulation of the organic light emitting display device. As shown in FIG. 2, the encapsulation substrate **200** may include a base film **210**, a connection layer **220**, and a metal oxide layer **230**.

The base film **210** may be formed of a metal material. According to one embodiment of the present invention, the base film **210** included in the encapsulation substrate **200** may be formed of a metal material containing magnesium (Mg).

In the present invention, the base film **210** is formed of the metal material containing magnesium (Mg). This is because magnesium (Mg) enables a heat insulating function owing to high thermal conductivity. Thus, since the base film **210** included in the encapsulation substrate **200** is formed of the metal material containing magnesium (Mg), the organic light emitting display device of the present invention does not require a heat insulating plate such as a related art fan or heat pipe so that it is possible to realize thinness and lightness in the organic light emitting display device of the present invention.

The connection layer **220** is formed on a first surface corresponding to one surface of the base film **210** confronting the substrate **100**. The connection layer **220** is electrically connected with the second electrode **190** formed on the substrate **100** through the auxiliary electrode **300**.

Accordingly, the connection layer **220** may be formed of a conductive metal material. According to one embodiment of the present invention, the connection layer **220** may be formed of an alloy using magnesium (Mg) which is the metal materials for the base film **210** and any one among argentum (Ag), titanium (Ti), tungsten (W), and iron (Fe).

According to one embodiment of the present invention, the connection layer **220** may be formed by performing a plasma treatment on the first surface of the base film **210** through the use of any one metal material selected from argentum (Ag), titanium (Ti), tungsten (W) and iron (Fe).

Then, the metal oxide layer **230** is formed on a second surface of the base film **210** which is opposite to the first surface of the base film **210**, wherein the connection layer **220** is formed on the first surface of the base film **210**. In the present invention, the metal oxide layer **230** is formed on the second surface of the base film **210**. This is because such structure facilitates to insulate the base film **210** from the external, and also to uniformly oxidize the entire area of the base film **210** of magnesium (Mg).

According to one embodiment of the present invention, the metal oxide layer **230** may be formed by anodizing the second surface of the base film **210**.

In this case, the above anodizing is a plating technique. That is, under the condition that the second surface of the base film **210** is immersed in electrolytic solution, an electric current is applied to the base film **210** functioning as an anode, whereby the second surface of the base film **210** is oxidized by oxygen generated from the anode.

In the present invention, the base film **210** is formed at a predetermined thickness by the use of magnesium (Mg). Thus, instead of oxidizing the entire area of the base film **210**, only the second surface of the base film **210** is changed into magnesium oxide (MgO), and the metal oxide layer **230** is formed on the second surface of the base film **210**.

In the above embodiment of the present invention, the metal oxide layer **230** is formed by the anodizing, but not limited to this method. The metal oxide layer **230** may be formed by various methods. For example, the metal oxide layer **230** may be formed by performing a plasma treatment on the second surface of the base film **210**.

In the present invention, the surface of the encapsulation substrate **200**, which confronts the substrate **100**, is formed of a conductive alloy, and is also electrically connected with the second electrode **190**, thereby reducing a resistance of the second electrode **190**, and preventing a voltage drop.

Also, since the base film **210** of the encapsulation substrate **200** is formed of magnesium (Mg) with good thermal conductivity, the organic light emitting display device of the present invention can improve heat insulating efficiency without using additional heat insulating plate. In addition, the additional heat insulating plate is not used in the organic light emitting display device of the present invention so that it is possible to realize thinness and lightness in the organic light emitting display device according to the present invention.

Then, the auxiliary electrode **300** electrically connects the second electrode **190** with the encapsulation substrate **200**. As shown in FIG. 2, the auxiliary electrode **300** may include a barrier **310** and a connection electrode **320**.

The barrier **310** having a predetermined height is formed in a non light-emission area of the substrate **100** so that the connection electrode **320** is brought into contact with the encapsulation substrate **200**. According to one embodiment of the present invention, as shown in FIG. 4, the barrier **310** may be formed in a closed loop of a frame shape in the circumference of light-emission area on the substrate **100**.

If satisfying that the barrier **310** has the predetermined height enabling to bring the connection electrode **320** into contact with the encapsulation substrate **200**, the barrier **310** may be formed of any material without limitation.

According to one embodiment of the present invention, the barrier **310** may be formed in the same layer structure as that of the thin film transistor by the use of material for forming the thin film transistor, or may be formed by the use of some layers among the layers included in the thin film transistor.

Also, the barrier **310** may be formed by additionally depositing at least one of the planarization layer **160**, the first electrode **170**, and the bank layer **175** on at least some layers among the layers included in the thin film transistor.

According to a first example, the barrier **310** may have a layer structure in such a manner that the gate electrode **110** is formed, the gate insulating film **120** is formed on the gate electrode **110**, the active layer **130** is formed on the gate insulating film **120**, the etch stopper **140** is formed on the active layer **130**, the source and drain electrodes **150a** and **150b** are formed on the etch stopper **140**, the passivation film **160** is formed on the source and drain electrodes **150a** and **150b**, and the planarization layer **165** is formed on the passivation film **160**.

According to a second example, the barrier **310** may have a layer structure in such a manner that the first electrode **170** and the bank layer **175** are sequentially deposited on the layer structure shown in the above first example, or may have a layer structure in such a manner that any one of the first electrode **170** and the bank layer **175** is additionally deposited on the layer structure shown in the above first example.

In addition, the barrier **310** may have a layer structure in such a manner that the gate electrode **110**, the source and drain electrodes **150a** and **150b**, and the first electrode **170** are sequentially deposited; may have a layer structure in such a manner that the gate electrode **110**, the source and drain electrodes **150a** and **150b**, the first electrode **170**, and the bank layer **175** are sequentially deposited; may have a layer structure in such a manner that the gate electrode **110**, the gate insulating film **120**, the source and drain electrodes **150a** and **150b**, and the first electrode **170** are sequentially deposited; or may have a layer structure in such a manner that the gate electrode **110**, the gate insulating film **120**, the source and drain electrodes **150a** and **150b**, the first electrode **170**, and the bank layer **175** are sequentially deposited.

Then, the connection electrode **320** is formed on the barrier **310**, and is brought into contact with the encapsulation substrate **200**. According to one embodiment of the present invention, as shown in FIG. 2, the connection electrode **320** may be formed as one body with the second electrode **190**.

According to the connection electrode **320** of the present invention is formed as one body with the second electrode **190**, and is simultaneously brought into contact with the encapsulation substrate **200**, the second electrode **190** is electrically connected with the encapsulation substrate **200**, whereby a surface resistance of the second electrode **190** is reduced without increasing a thickness of the second electrode **190**, thereby preventing a voltage drop caused by the second electrode **190**.

Referring once again to FIG. 2, the sealing pattern **400** is interposed between the substrate **100** and the encapsulation substrate **200**, thereby bonding the substrate **100** and the encapsulation substrate **200** to each other. The sealing pattern **400** may vary in shape.

For example, as shown in FIGS. 2 to 4, the sealing pattern **400** may include a first sealing pattern **410** formed in a closed loop of a frame shape surrounding the auxiliary electrode **300** on the circumference of auxiliary electrode **300**, or may additionally include a second sealing pattern **420** for covering the light emission area inside the auxiliary electrode **300**.

Hereinafter, a method for manufacturing the organic light emitting display device according to one embodiment of the present invention will be described in detail as follows.

FIGS. 5A to 5D are cross sectional views illustrating a process for manufacturing the organic light emitting display device according to one embodiment of the present invention, which relate to a process for manufacturing the organic light emitting display device shown in FIGS. 2 and 3. Hereinafter, a detailed explanation for the material and structure of each element will be omitted.

First, as shown in FIG. 5A, the thin film transistor (T) is formed on the substrate **100**, and the first electrode **170** electrically connected with the thin film transistor (T) is formed on the substrate **100**. Then, the organic light emitting layer **180** is formed on the first electrode **170**.

In this case, the thin film transistor (T) may be manufactured by the general process for forming the thin film transistor (T). Also, the process for manufacturing the thin film transistor (T) is not a main point, whereby a detailed explanation for the manufacturing process of the thin film transistor (T) will be omitted.

Then, as shown in FIG. 5B, the barrier **310** is formed in the non light-emission area of the substrate **100**. According to one embodiment of the present invention, the barrier **310** may be formed in the closed loop of the frame shape in the circumference of light-emission area on the substrate **100**.

For convenience of explanation, FIG. 5B illustrates that the barrier **310** is formed after the thin film transistor (T), the first electrode **170**, and the organic light emitting layer **180**, but not limited to this method.

For example, the barrier **310** may be manufactured together with the thin film transistor (T), the first electrode **170**, and the organic light emitting layer **180**, at the same time; or may be manufactured during the process of forming the thin film transistor (T) before forming the first electrode **170** and the organic light emitting layer **180**.

For example, the barrier **310** may be formed in the same layer structure as that of the thin film transistor (T) by the use of material for forming the thin film transistor (T) during the process of forming the thin film transistor (T), or may be formed by additionally depositing at least one of the planarization layer **160**, the first electrode **170**, and the bank layer **175** on at least some layers among the layers included in the thin film transistor.

As shown in FIG. 5C, the second electrode **190** is formed on the substrate **100** including the organic light emitting layer **180** and the barrier **310**. The second electrode **190** is provided in such a manner that the second electrode **190** is commonly applied to all pixels without being divided by each pixel. In this case, the second electrode **190** provided on the barrier **310** forms the connection electrode **320**, whereby the auxiliary electrode **300** is formed on the substrate **100**.

Then, as shown in FIG. 5D, the substrate **100** and the encapsulation substrate **200** are bonded to each other by the use of sealing pattern **400**. In this case, the sealing pattern **400** may include the first sealing pattern **410** surrounding the auxiliary electrode **300** in the circumference of auxiliary electrode **300**, and the second sealing pattern **420** covering the light-emission area inside the auxiliary electrode **300**.

Meanwhile, when bonding the substrate **100** and the encapsulation substrate **200** to each other, the encapsulation substrate **200** is brought into contact with the auxiliary electrode **300**. According as the auxiliary electrode **300**, which is electrically connected with the second electrode **190**, is electrically connected with the encapsulation substrate **200**, it is possible to prevent the voltage drop caused by the resistance of the second electrode **190**.

According to one embodiment of the present invention, the encapsulation substrate **200** may be manufactured by

forming the connection layer **220** on the first surface of the base film **210** of magnesium (Mg) through the use of alloy of magnesium (Mg) and any one selected from argentum (Ag), titanium (Ti), tungsten (W) and iron (Fe); and forming the metal oxide layer **230** through the anodizing treatment on the second surface of the base film **210**. In this case, the connection layer **200** may be formed by performing the plasma treatment on the first surface of the base film **210**.

The first surface of the base film **210** indicates the surface being connected with the second electrode **190**, and the second surface of the base film **210** indicates the surface being opposite to the surface provided with the connection layer **220**.

In the above embodiment of the present invention, the metal oxide layer **230** is formed by the anodizing technique, but not limited to this method. The metal oxide layer **230** may be manufactured by the various methods. For example, the metal oxide layer **230** may be manufactured by performing the plasma treatment on the second surface of the base film **210**.

According to the present invention, the surface of the encapsulation substrate **200**, which confronts with the substrate **100**, is formed of a conductive alloy, and the surface of the encapsulation substrate **200** is electrically connected with the auxiliary electrode **300**, whereby it is possible to reduce the resistance of the second electrode **190**, and thus to prevent the voltage drop.

In the present invention, the base film **210** of the encapsulation substrate **200** is formed of the metal material containing magnesium (Mg) with good thermal conductivity. Thus, it is possible to improve the heat insulating efficiency in the organic light emitting display device even though there is no additional heat insulating plate. In addition, the organic light emitting display device of the present invention does not require the additional heat insulating plate so that it is possible to realize thinness and lightness in the organic light emitting display device of the present invention.

According to the present invention, the encapsulation substrate **200** of the metal material is electrically connected with the second electrode **190** so that it is possible to prevent the voltage drop, which is caused by the resistance increase of the second electrode **190**, without increasing the thickness of the second electrode **190**, thereby reducing the manufacturing cost of the organic light emitting display device.

According as the voltage drop, which is caused by the resistance increase of the second electrode **190**, is prevented, it is possible to prevent the power consumption from being increased, and also to realize the uniform luminance, thereby improving reliability of the organic light emitting display device.

Also, since the encapsulation substrate **200** of the metal material serves the heat insulating function, there is no need to provide the additional heat insulating plate, thereby maximizing lightness and thinness in the organic light emitting display device.

It will be apparent to those skilled in the art that various modifications and variations can be made in the present invention without departing from the spirit or scope of the inventions. Thus, it is intended that the present invention covers the modifications and variations of this invention provided they come within the scope of the appended claims and their equivalents.

What is claimed is:

1. An organic light emitting display device comprising:
 - a substrate;
 - a first electrode on the substrate;

11

an organic light emitting layer on the first electrode;
 a second electrode on the substrate including the organic light emitting layer;
 an encapsulation substrate confronting the substrate; and
 an auxiliary electrode in a non light-emission area of the substrate, the auxiliary electrode including:
 a barrier extending from the substrate towards the encapsulation substrate without contacting the encapsulation substrate such that a space exists between a top of the barrier and the encapsulation substrate, and
 a connection electrode extended from the second electrode and being formed on and around the barrier to fill the space between the top of the barrier and the encapsulation substrate such that the auxiliary electrode directly contacts the substrate and the encapsulation substrate,
 wherein the encapsulation substrate is formed of a metal material, and is electrically connected with the second electrode,
 wherein the second electrode and the encapsulation substrate are electrically connected to each other through the auxiliary electrode,
 wherein the auxiliary electrode is not disposed in a region between pixels, and
 wherein the encapsulation substrate does not include an insulating material.

2. The device of claim 1, wherein the encapsulation substrate includes:
 a base film formed of a metal material including magnesium (Mg);
 a connection layer formed of a conductive metal material on a first surface of the base film so as to enable an electrical connection with the second electrode; and
 a metal oxide layer formed on a second surface of the base film in opposite to the first surface of the base film.

3. The device of claim 2, wherein the connection layer is formed of an alloy of magnesium (Mg) and at least any one metal material selected from argentine (Ag), titanium (Ti), tungsten (W), and iron (Fe).

4. The device of claim 2, wherein the metal oxide layer is formed by performing an anodizing or plasma treatment on the second surface of the base film.

5. The device of claim 1, wherein the barrier is formed in a closed loop surrounding a light-emission area on the non light-emission area of the substrate.

6. The device of claim 2, further comprising:
 a sealing pattern interposed between the substrate and the encapsulation substrate to bond the substrate and the encapsulation substrate to each other.

12

7. The device of claim 6, wherein the sealing pattern includes:
 a first sealing pattern surrounding the auxiliary electrode along a circumference of the auxiliary electrode.

8. The device of claim 7, wherein the first sealing pattern is provided in a closed loop of a frame shape.

9. The device of claim 7, wherein the sealing pattern further includes:
 a second sealing pattern covering a light-emission area.

10. The device of claim 9, wherein the sealing pattern is interposed between the second electrode and the encapsulation substrate in the light-emission area.

11. The device of claim 9, wherein the second sealing pattern is surrounded by the auxiliary electrode.

12. An organic light emitting display device comprising:
 a substrate;
 a first electrode on the substrate;
 an organic light emitting layer on the first electrode;
 a second electrode on the substrate including the organic light emitting layer;
 an encapsulation substrate confronting the substrate; and
 an auxiliary electrode in a non light-emission area of the substrate, wherein the auxiliary electrode includes:
 a barrier formed in a closed loop surrounding a light-emission area on the non light-emission area of the substrate,
 the barrier extending from the substrate towards the encapsulation substrate without contacting the encapsulation substrate such that a space exists between a top of the barrier and the encapsulation substrate, and
 a connection electrode extended from the second electrode towards the substrate to directly contact the substrate, and then extended toward the encapsulation substrate and formed on and around the barrier to fill the space between the top of the barrier and the encapsulation substrate such that the auxiliary layer directly contacts the substrate and the encapsulation substrate,
 wherein the encapsulation substrate is formed of a metal material, and is electrically connected with the second electrode,
 wherein the second electrode and the encapsulation substrate are electrically connected to each other through the auxiliary electrode,
 wherein the auxiliary electrode is not disposed in a region between pixels, and
 wherein the encapsulation substrate does not include an insulating material.

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摘要(译)

讨论了一种防止电压降的有机发光显示装置，其中发光显示装置包括基板;基板上的第一电极;第一电极上的有机发光层;基板上的第二电极，包括有机发光层;面对基板的封装基板，其中封装基板由金属材料形成，并与第二电极电连接。

